



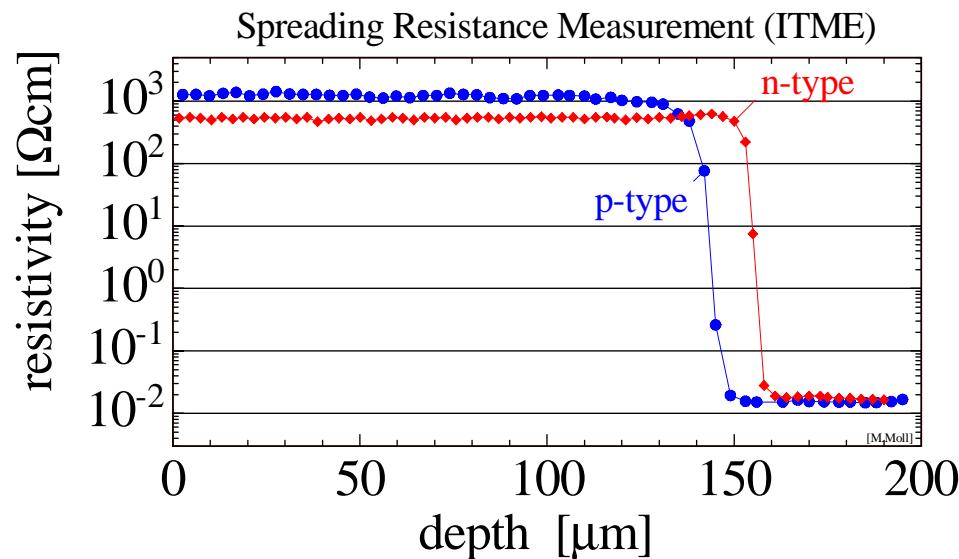
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# **Epitaxial silicon detectors irradiated with protons and neutrons**

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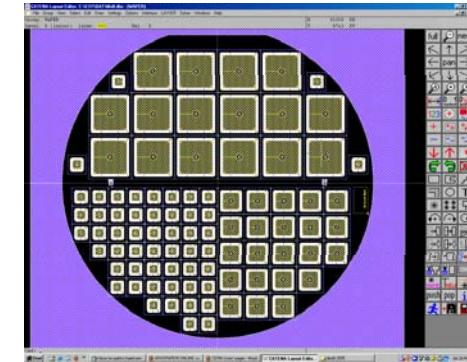
- **Produced by ITME** (Institute of Electronic Materials Technology, Warsaw, Poland)
  - 100 mm wafer
- **n-type silicon**
  - Epi-layer: 150 $\mu$ m, <111>, P-doped, ~500  $\Omega$ cm
  - Substrate: 525 $\mu$ m, <111>, Sb-doped, 0.015  $\Omega$ cm
- **p-type silicon**
  - Epi-layer: 150 $\mu$ m, <111>, P-doped, ~1000  $\Omega$ cm
  - Substrate: 525 $\mu$ m, <111>, B-doped, 0.015  $\Omega$ cm





- **HIP-004-C**

- Produced by Helsinki Institute of Physics, Helsinki, Finland
- Size  $0.25 \times 0.25 \text{ cm}^2$ , thickness 150  $\mu\text{m}$
- n-type
- Depletion voltage (CV) before irradiation:  
 $V_{\text{dep}} = 147.4 \pm 3.6 \text{ V}$

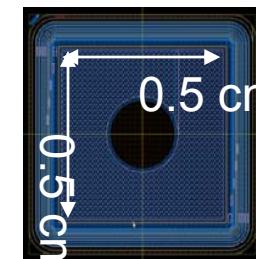


- **CNM-11**

- Produced by Centro National de Microelectronics, Barcelona, Spain
- Size  $0.5 \times 0.5 \text{ cm}^2$ , thickness 150  $\mu\text{m}$
- n-type
- Depletion voltage (CV) before irradiation:  
 $V_{\text{dep}} = 154.6 \pm 7.5 \text{ V}$

- **CNM-22**

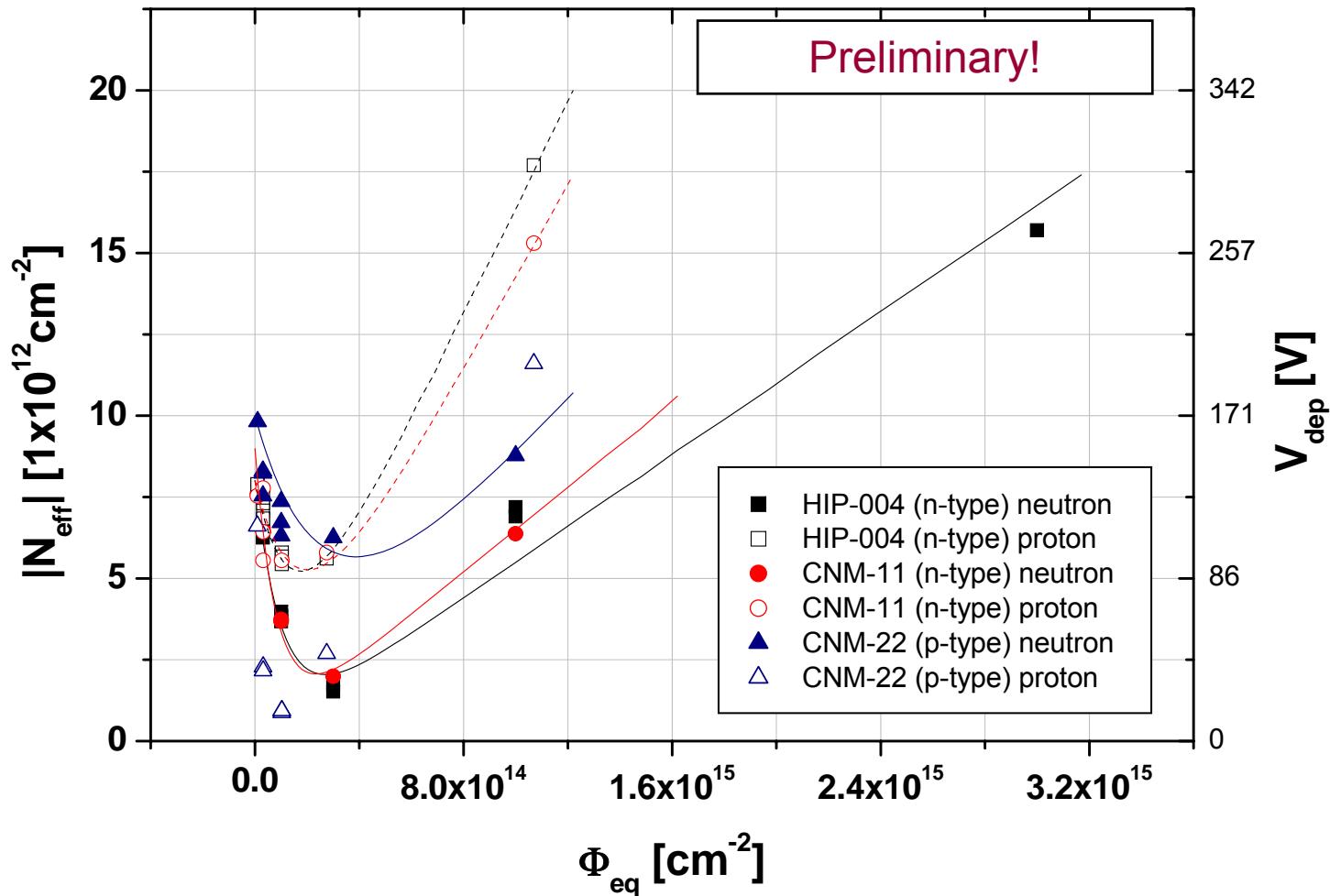
- Size  $0.5 \times 0.5 \text{ cm}^2$ , thickness 150  $\mu\text{m}$
- p-type
- Depletion voltage (CV) before irradiation:  
 $V_{\text{dep}} = 213.7 \pm 12.7 \text{ V}$

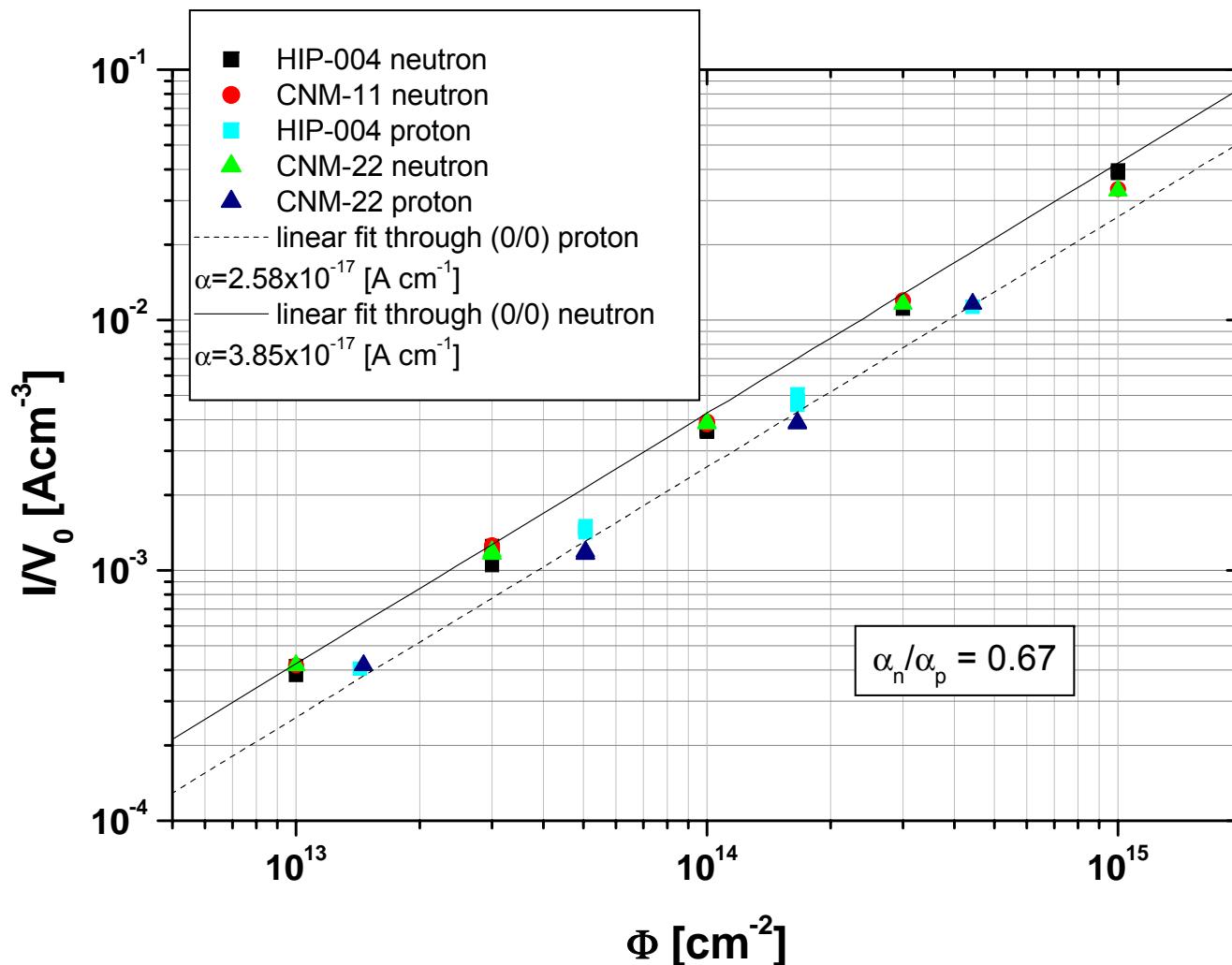


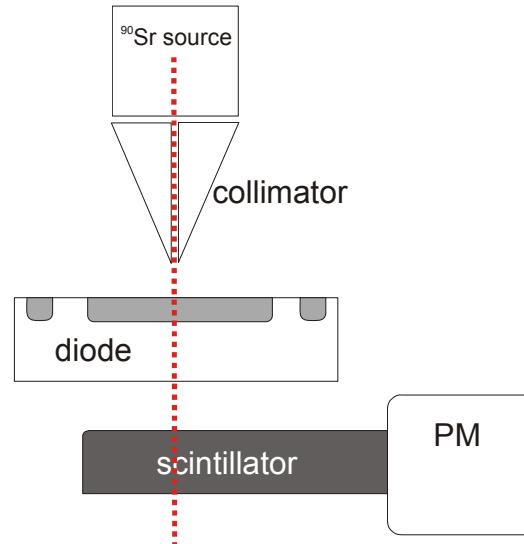


- **Irradiation**
  - 1 MeV neutrons in Ljubljana
  - 24 GeV/c protons at CERN
- **Annealing**
  - 4 minutes at 80°C
- **CV/IV**
  - Measured at room temperature in parallel mode at 10kHz
- **CCE**
  - NIKHEF setup

# Depletion voltage (CV)







### NIKHEF setup by Fred Hartjes

signal shaping time: 2.5  $\mu$ s

guard ring connected to ground

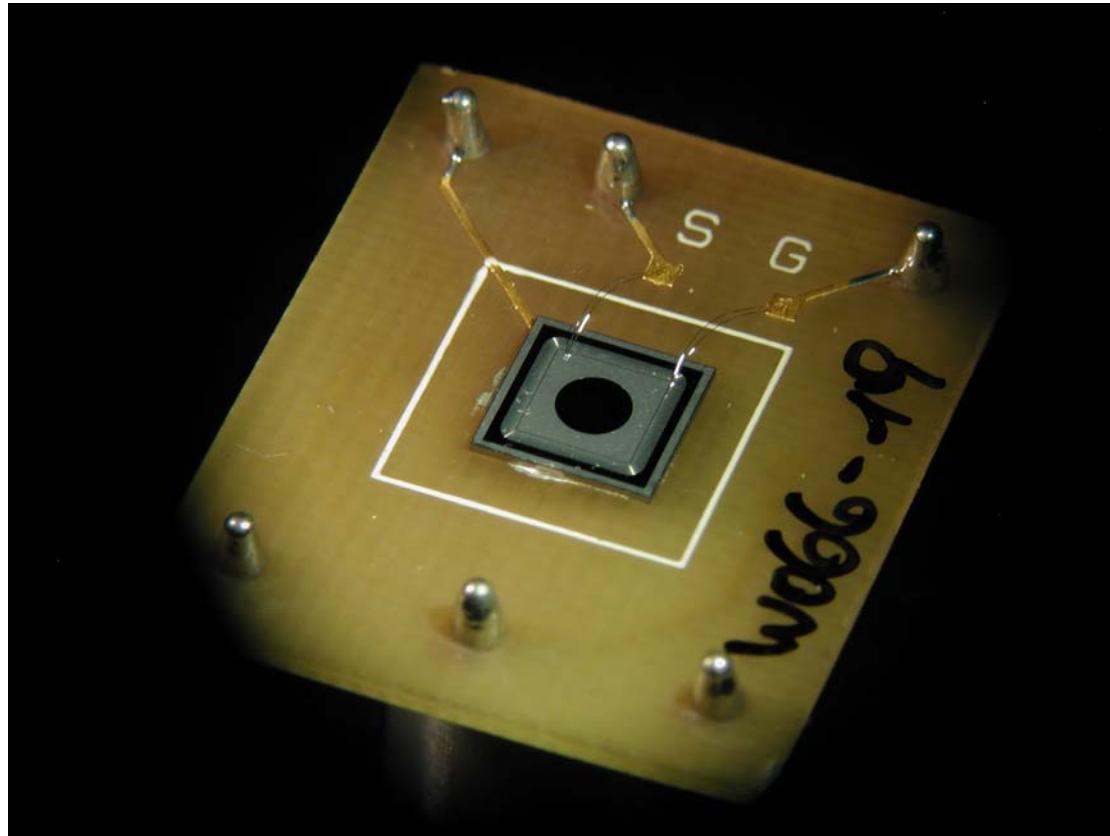


### Temperature control:

- internal cooling with peltier
- whole box can be put into freezer

### Temperature measurement:

- directly on sample board
- in box with additional humidity sensor



- Detector glued on board with silver glue
- Guard ring connected to ground



- all detectors were measured at  $-20 \pm 1^\circ\text{C}$  (only external cooling)
- humidity in the box was 18-30% (flushed with dry nitrogen)
- Repeated gain measurements showed a gain of 247 e<sup>-</sup>/mV for these conditions

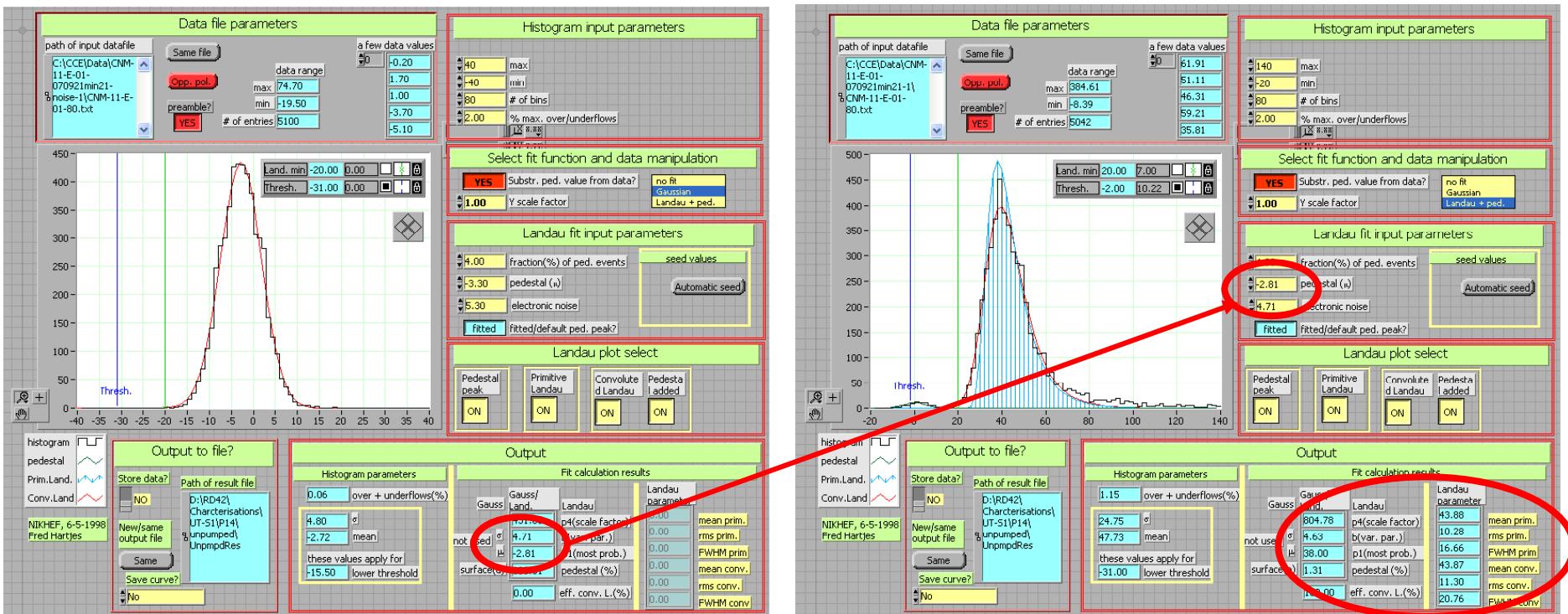




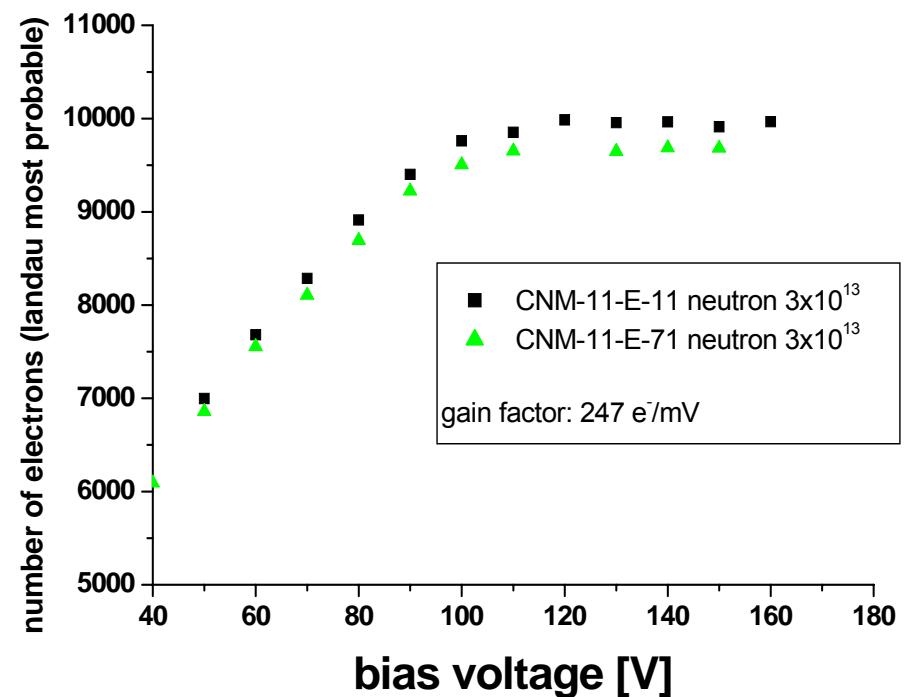
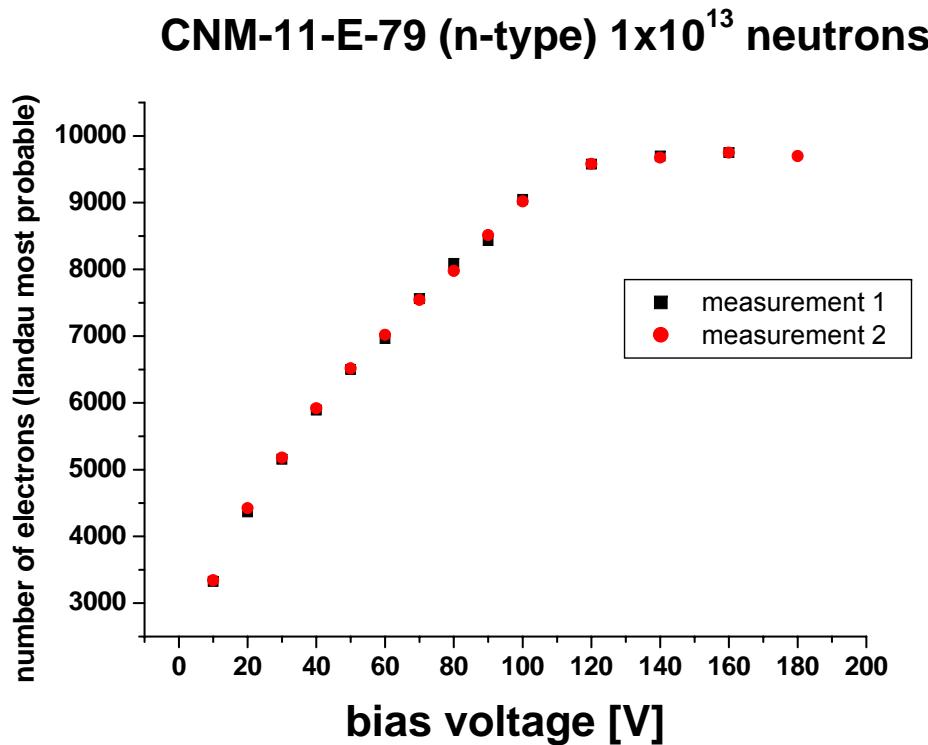
## Example: CNM-11-01 (n-type)

irradiation:  $\Phi = 1 \times 10^{14} \text{ p/cm}^2$   
 bias: 80 V

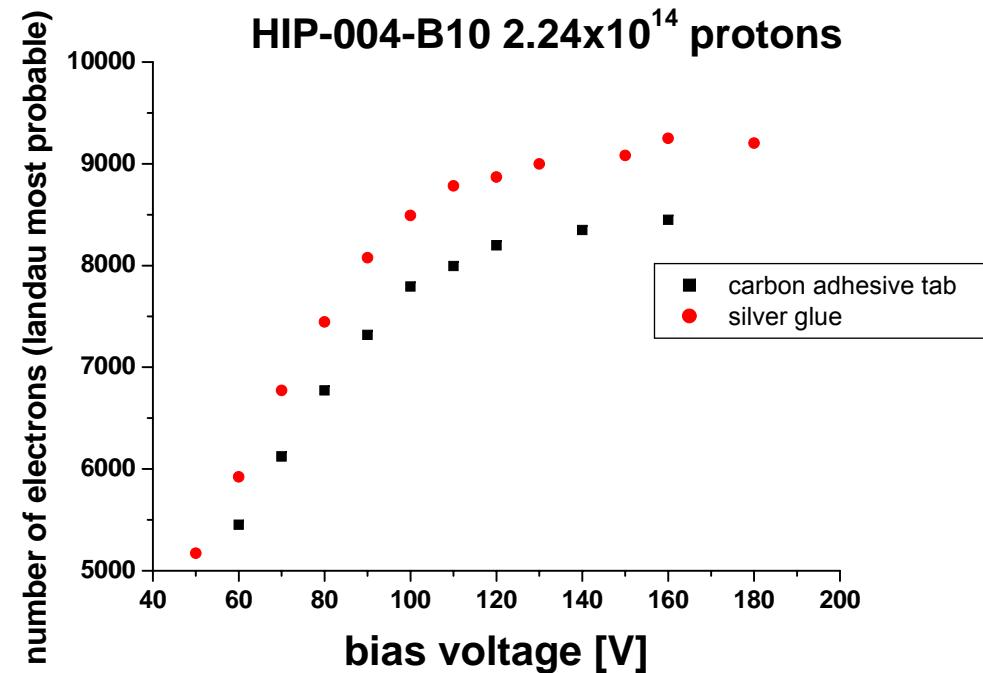
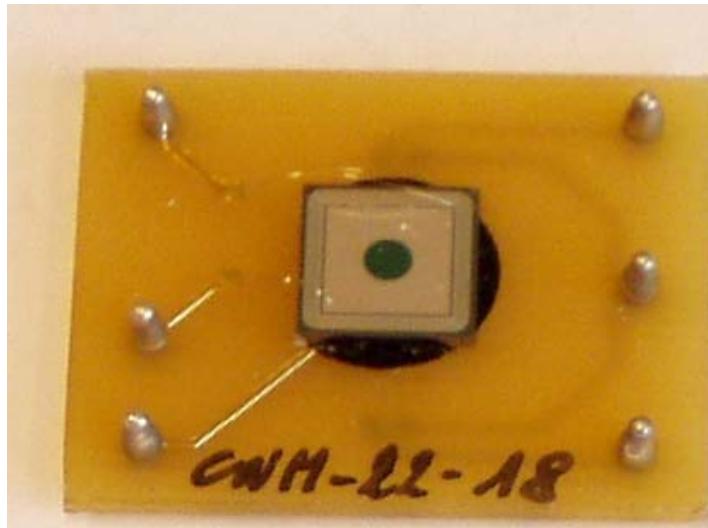
temperature: -21 °C



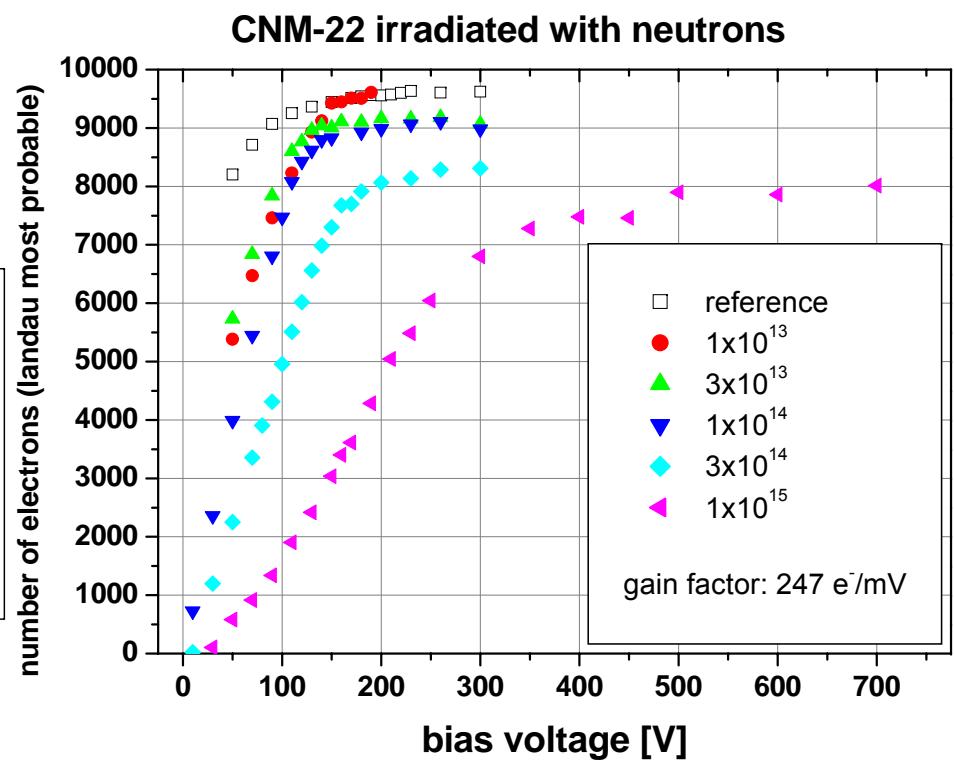
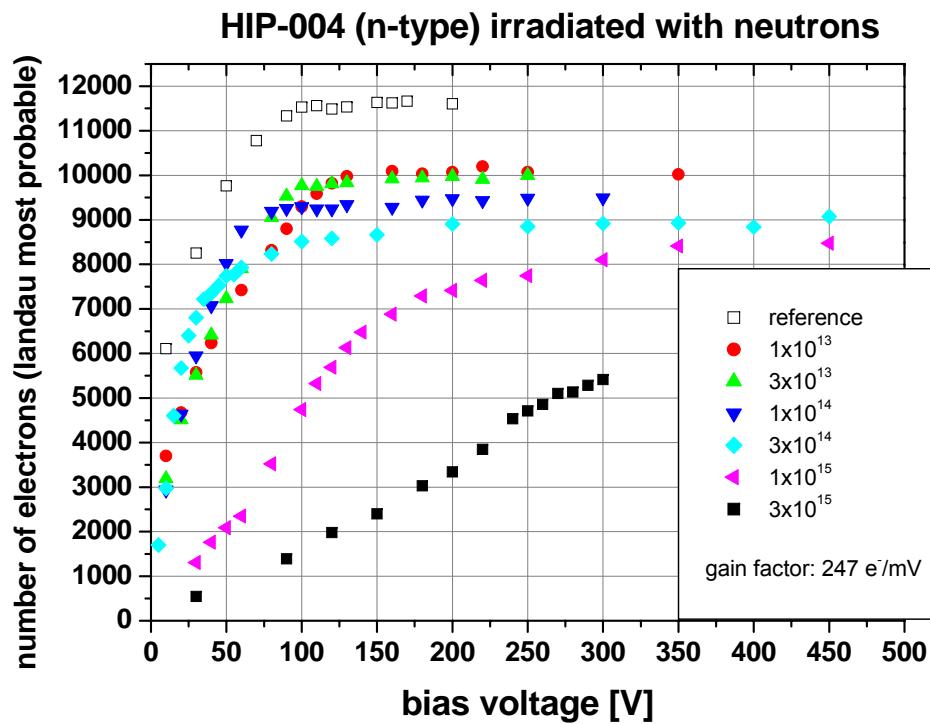
Noise/pedestal measurement for each bias point => values used for deconvoluted landau distribution

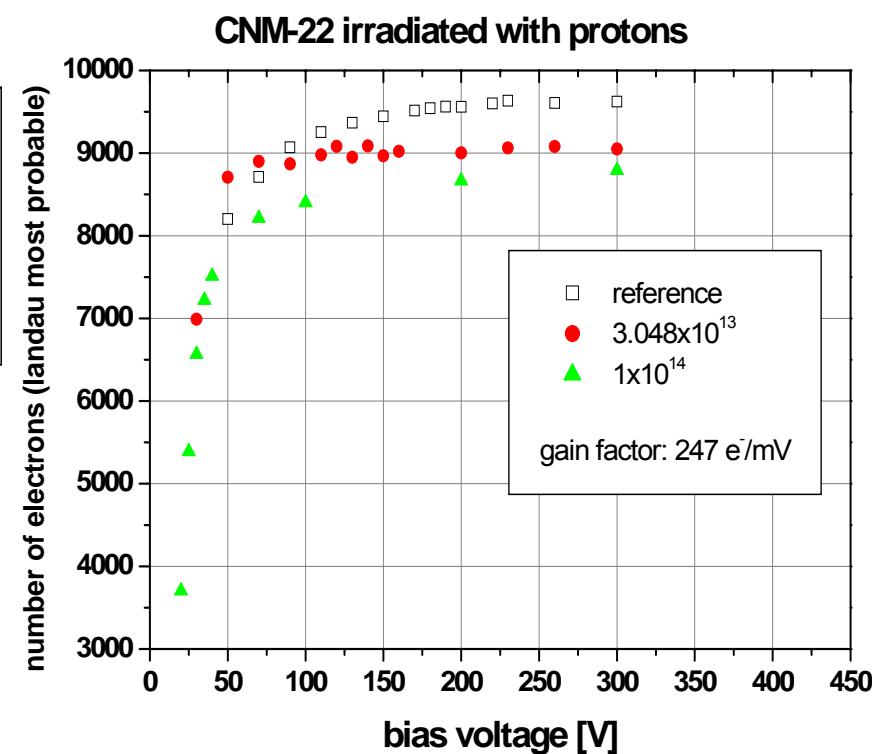
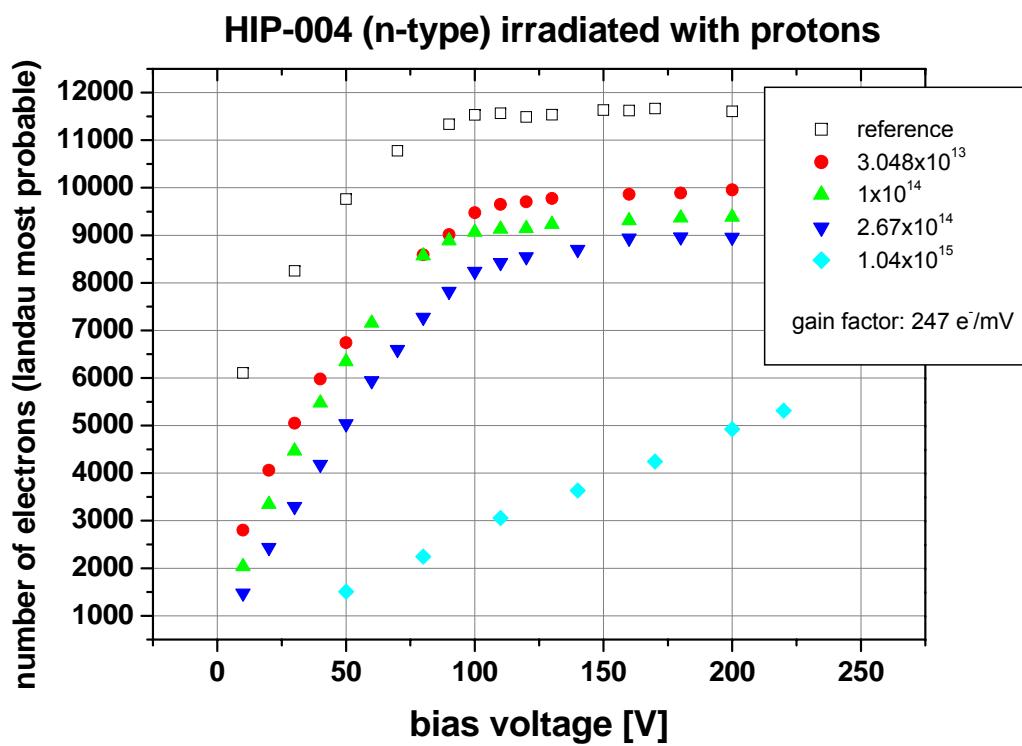


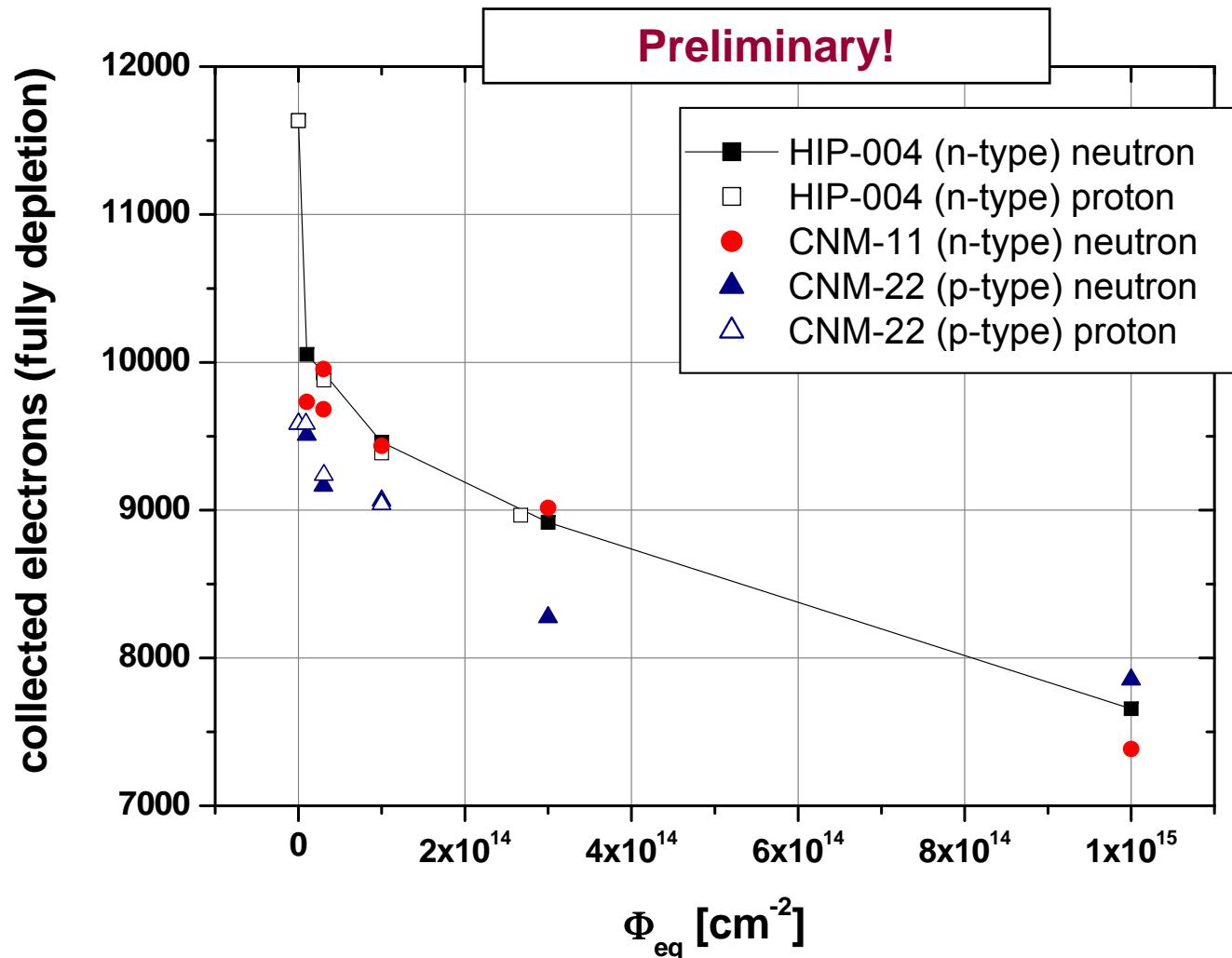
- Detector was **taken out** of the setup and remounted between measurements
- Temperature and humidity were approximately the same
- Different detectors, same fluence
- Temperature and humidity were approximately the same
- 3-4 % difference over depletion

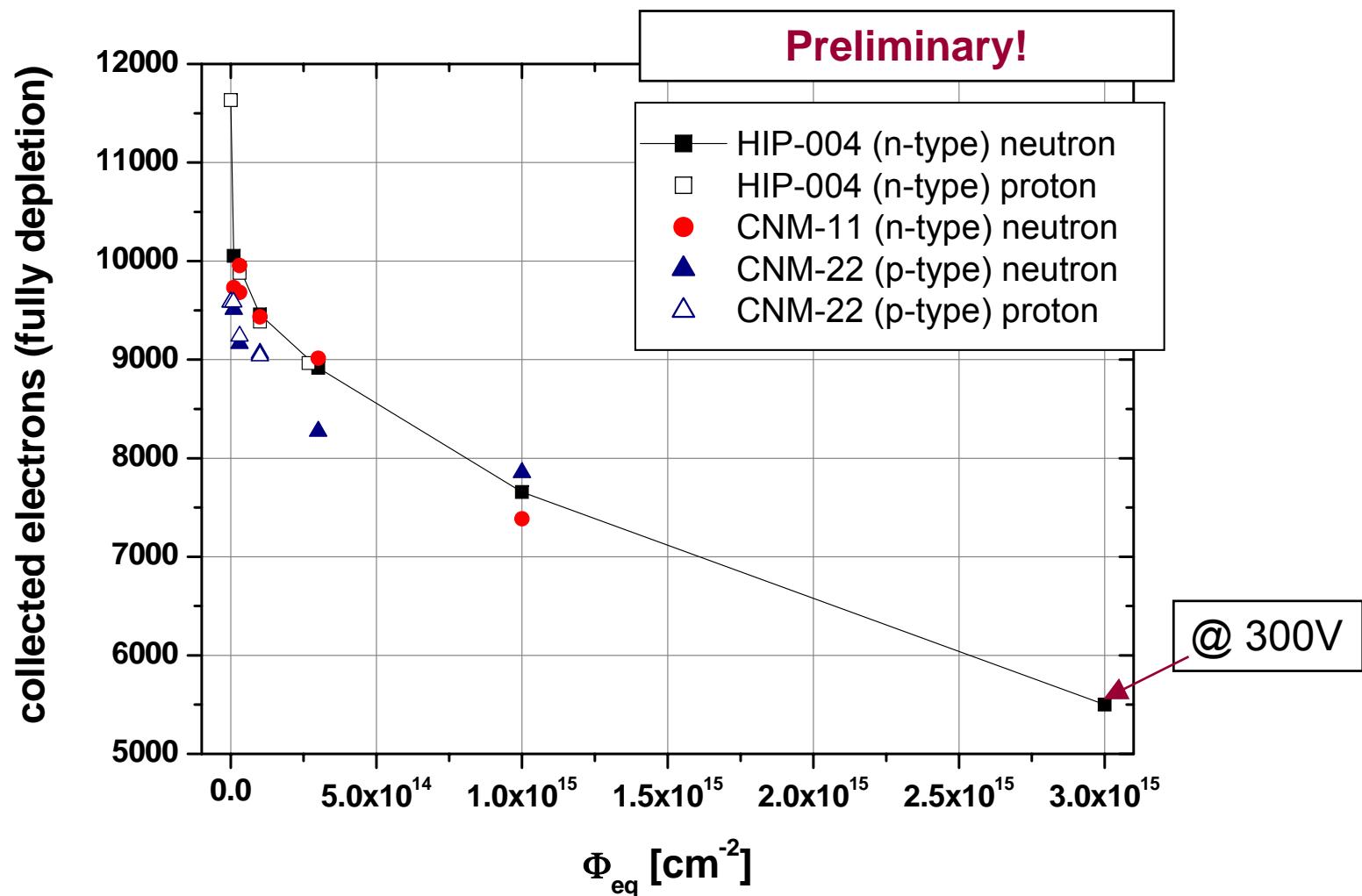


- The same detector was first measured fixed to the board with **carbon adhesive tabs**, then removed from the board and fixed with **silver glue**.
- The environmental conditions were approximately the same for both measurements (- 21°C, 20%).
- 8-10% difference over depletion
- We didn't investigate the problem further (CV, IV...) and abandoned the carbon adhesive tabs.











## Summary

- Increase of depletion voltage different for different manufacturers
- Increase of depletion voltage faster for proton irradiation
- Unusual drop in CCE at low fluences, for both neutron and proton irradiation

## Outlook

- Finish the measurements for the proton irradiated series and add a few more fluence points between  $5 \times 10^{14}$  p/cm<sup>2</sup> and  $3 \times 10^{15}$  p/cm<sup>2</sup>
- A set of detectors was already irradiated with protons at fluences between  $1 \times 10^{12}$  p/cm<sup>2</sup> and  $1 \times 10^{13}$  p/cm<sup>2</sup> to investigate the drop in the CCE further

# Carbon adhesive tabs

